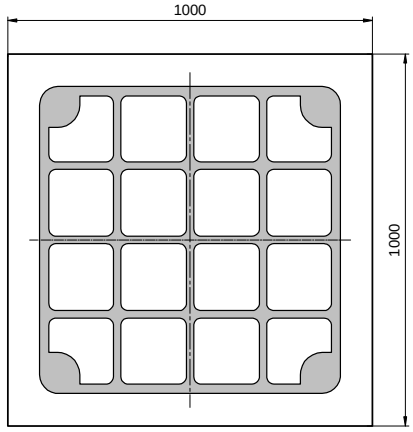
LED - Chip

ELC-870-21

26.04.2012 rev. 03

Radiation	Type	Technology	Electrodes
Infrared	DDH	AlGaAs/AlGaAs	N (cathode) up



typ. dimensions (µm)

typ. thickness
180 µm

cathode
gold alloy, 1.5 µm

anode
gold alloy, 0.5 µm
structured, 25% covered

Optical and Electrical Characteristics

T_{amb} = 25℃, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F = 20 mA	V_F		1.3	1.5	V
Forward voltage[1]	I_F = 350 mA	V_F		1.5	1.8	V
Reverse voltage	I_R = 100 µA	V_R	5			V
Radiant power	I_F = 20 mA	Φ_e	3.5	5		mW
Radiant power[1]	I_F = 350 mA	Φ_e	70	90		mW
Peak wavelength	I_F = 20 mA	λ_P	860	870	880	nm
Spectral bandwidth at 50%	I_F = 20 mA	$\Delta\lambda_{0.5}$		35		nm
Switching time	I_F = 20 mA	t_r, t_f		20		ns

[1]Measured on bare chip glued on a Ø 8 x 1mm Cu header with JENOPTIK Polymer Systems equipment

Labeling

Type	Lot	Φ_e(typ) [mW]	V_F(typ) [V]	λ_P(typ) [nm]	Quantity
ELC-870-21					

Packing: Chips on adhesive film with wire-bond side on top

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